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Patent and Trademark OfficeAttorney's Docket No.
10559-678002Application No.
10/620,829**Information Disclosure Statement
by Applicant**

(Use several sheets if necessary)

Applicant
Keshavarzi et al.Filing Date
July 16, 2003

Group Art Unit

(37 CFR 1.98(b))

U.S. Patent Documents

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
/TXL/	AA	5,105,078	04/1992	Nochise, et al.	250	223R	
↓	AB	5,694,448	12/1997	Morcom	378	98.8	
↓	AC	6,141,243	10/2000	Aslam, et al.	365	185.01	
↓	AD	6,388,494	05/2002	Kindt, et al.	327	307	
↓	AE	6,404,269	06/2002	Voldman	327	534	
/TXL/	AF	US-2001-0019285-A1	09/2001	Lin, et al.	327	534	
	AG						
	AH						
	AI						
	AJ						

Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
	AK							
	AL							
	AM							
	AN							
	AO							

Other Documents (include Author, Title, Date, and Place of Publication)

Examiner Initial	Desig. ID	Document
/TXL/	AP	Kelleher et al., IEEE, "Development of the Radiation Sensitivity of PMOS Dosimeters - Développement de la Sensibilité aux Radiations de Dosimètres PMOS", pp. 342-346 (1992)
↓	AQ	Ma et al., "Ionizing Radiation Effects in Mos Devices and Circuits", John Wiley & Sons, pp. 262, 265-267 (1989)
↓	AR	Moreno et al., "CMOS Radiation Sensor with Binary Output", IEEE Transactions on Nuclear Science, Vol. 42, No. 3, pp. 174-178, June 1995
/TXL/	AS	Ray et al., IEEE Transactions on Nuclear Science, "CRRES Dosimetry Results and Comparisons Using the Space Radiation Dosimeter and P-Channel MOS Dosimeters", Vol. 39, No. 6, pp. 1846-1850, December, 1992

Examiner Signature

/Thanh X Luu/

Date Considered

04/23/2007

EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.